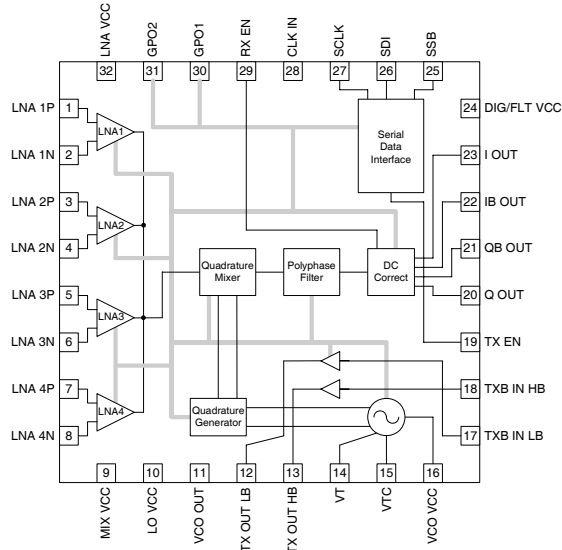


**Features**

- GSM850, EGSM, DCS & PCS Operation
- Supports Both VLIF & DCR Modes
- Integrated RF VCO
- Integrated LNA's Support up to Four RF Bands
- EDGE Receive Compatible

**Applications**

- EGSM/DCS Handsets
- EGSM/DCS/PCS Handsets
- GSM850/PCS Handsets
- GSM850/EGSM/DCS/PCS Handsets



Functional Block Diagram

**Product Description**

The RF2722 is a highly-integrated receiver IC supporting GSM, GPRS, and EDGE cellular standards in the GSM850, EGSM, DCS, and PCS bands. The RF2722 supports both very-low intermediate frequency (VLIF) as well as direct conversion receive (DCR) architectures, reducing external component count and eliminating the need for IF SAW and RF interstage filters without compromising performance. The IC includes: four LNA's for multi-band support; an integrated voltage controlled oscillator (VCO); automatic gain control (AGC); a quadrature downconverting mixer; and, low and high band transmit buffers. Chip functionality, including IF AGC setting, is controlled through a three-wire serial data interface (SDI). The RF2722 is part of the POLARIS™ TOTAL RADIO™ solution.

**Ordering Information**

RF2722	GSM/GPRS/EDGE Receiver
RF2722PCBA-41X	Fully Assembled Evaluation Board

**Optimum Technology Matching® Applied**

- |                                      |                                      |                                     |                                   |
|--------------------------------------|--------------------------------------|-------------------------------------|-----------------------------------|
| <input type="checkbox"/> GaAs HBT    | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS   | <input type="checkbox"/> Si CMOS    |                                   |
| <input type="checkbox"/> InGaP HBT   | <input type="checkbox"/> SiGe HBT    | <input type="checkbox"/> Si BJT     |                                   |

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## Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage	-0.5 to +3.6	V
Storage Temperature	-40 to +150	°C
Input Voltage, any pin	3.6	V



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Operating Range</b>					Temp = -30 °C to +85 °C, V <sub>CC</sub> = 2.7V to 3.0V, all specifications referenced to 50Ω, unless specified differently.
Temperature (T <sub>OP</sub> )	-30		+85	°C	
Frequency Range					
GSM850 RX	869		894	MHz	Low Band
GSM850 TX	824		849	MHz	Low Band
EGSM RX	925		960	MHz	Low Band
EGSM TX	880		915	MHz	Low Band
DCS RX	1805		1880	MHz	High Band
DCS TX	1710		1785	MHz	High Band
PCS RX	1930		1990	MHz	High Band
PCS TX	1850		1910	MHz	High Band
Supply Voltage (V <sub>CC</sub> )	2.7	2.75	3.0	V	Pins 9 (MIXVCC), 10 (LOVCC), 16 (VCOVCC), 24 (DIG/FLT VCC), and 32 (LNAVCC).
Power Down Current			10	μA	RX EN = 0
Active Current					
<i>RX VLIF Mode</i>					
Low Band (850/950MHz)	64	77	91	mA	All circuits on, (LNA_CURR = 10, MIX_CURR = 10)
High Band (1800/1900MHz)	63	76	90	mA	All circuits on, (LNA_CURR = 00, MIX_CURR = 00)
<i>RX DCR Mode</i>					
Low Band (850/950MHz)	62.5	75.5	89.5	mA	All circuits on, (LNA_CURR = 10, MIX_CURR = 10)
High Band (1800/1900MHz)	61.5	74.5	88.5	mA	All circuits on, (LNA_CURR = 00, MIX_CURR = 00)
<i>TX Mode</i>					
Low Band (850/950MHz)		19.5	25	mA	V <sub>CC</sub> = 2.8V, P <sub>IN</sub> = +4dBm
High Band (1800/1900MHz)		24.5	32	mA	
<b>Receiver System</b>					Low side LO injection for all bands. Except where noted, receiver specifications defined from LNA input with I or Q channel differential as output.
Cascaded Noise Figure					
Low Band (850/950MHz)		2.8		dB	+25 °C, LNA_BYP = 0
High Band (1850/1950MHz)		3.2		dB	+25 °C, LNA_BYP = 0

Low Band (850/950MHz)			4.8	dB	-30-85°C, LNA_BYP=0
High Band (1850/1950MHz)			5.2	dB	-30-85°C, LNA_BYP=0
Noise Figure with 3MHz Blocker					
Low Band (850/950MHz)		3.8	4.8	dB	+25°C; -26dBm at LNA input.
High Band (1800/1900MHz)		4.7	5.7	dB	+25°C; -29dBm at LNA input.
Cascaded IIP3					
Low Band (850/950MHz)		-12		dBm	+25°C; LNA_BYP=0; Interferers at 0.8MHz and 1.6MHz
High Band (1850/1950MHz)		-11		dBm	
Low Band (850/950MHz)	-15			dBm	-30-85°C; LNA_BYP=0; Interferers at 0.8MHz and 1.6MHz
High Band (1850/1950MHz)	-14			dBm	

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Receiver System, cont'd</b>					
Cascaded IIP2 (VLIF Improvement not included)					1 tone (IIP2 <sub>1</sub> )/2 tone (IIP2 <sub>1</sub> ) LNA_BYP=0
Low Band (850/950MHz)	50	58		dBm	1 tone
	44	52		dBm	2 tone
High Band (1850/1950MHz)	50	58		dBm	1 tone
	44	52		dBm	2 tone
Cascaded P1dB					
Low Band (850/950MHz)	-22	-20		dBm	Minimum Gain
High Band (1850/1950MHz)	-23	-21		dBm	Minimum Gain
Cascaded Gain					
Low Band (850/950MHz)	54.5	57.5	60.5	dB	LNA_BYP=0; Polyphase Gain=0/12.6/7.4/1/8.4dB
High Band (1850/1950MHz)	53.5	56.5	59.5	dB	LNA_BYP=0; Polyphase Gain=0/12.6/7.4/1/8.4dB
Gain Compression with 3MHz Blocker					
Low Band (850/950MHz)			1.5	dB	+25 °C; LNA_BYP=0; -26dBm at LNA input, with gain settings for a -99dBm wanted signal.
High Band (1850/1950MHz)			1.0	dB	+25 °C; LNA_BYP=0; -29dBm at LNA input, with gain settings for a -99dBm wanted signal.
LNA Gain Step					
Low Band (850/950MHz)	15	16	17	dB	LNA_BYP=1
High Band (1850/1950MHz)	17	18	19	dB	LNA_BYP=1
LO Leakage					
Low Band (850/950MHz)		-110	-100	dBm	At the LNA input.
High Band (1850/1950MHz)		-110	-100	dBm	At the LNA input.
2LO Suppression					LNA_BYP=0
Low Band (850/950MHz)		-22	-20	dB	
High Band (1850/1950MHz)		-24	-22	dB	
3LO Suppression					LNA_BYP=0
Low Band (850/950MHz)		-6	-4	dB	
High Band (1850/1950MHz)		-16	-14	dB	
5LO Suppression					LNA_BYP=0
Low Band (850/950MHz)		-22	-20	dB	
High Band (1850/1950MHz)		-45	-43	dB	
Image Balance					
Low Band (850/950MHz)	32	36		dB	
High Band (1850/1950MHz)	32	36		dB	
LNA Input Impedance					
Low Band (850/950MHz)		82-j156		Ω	
High Band (1850/1950MHz)		38-j66		Ω	
LNA Input Return Loss					
Low Band (850/950MHz)			-10	dB	With external match to 100Ω
High Band (1850/1950MHz)			-10	dB	With external match to 100Ω
Absolute Gain Accuracy	-3.2		+3.2	dB	For any recommended AGC setting across frequency and temperature in a single band, for power levels between -110dBm and -48dBm, assuming 1 gain calibration point per band.

Relative Gain Accuracy	-1		+1	dB	For any 20dB gain step, using recommended AGC gain settings for receive power levels in the range -110dBm and -48dBm.
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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>VCO+LO Chain</b>					Buffers, divide-by-2, divide-by-4, divide-by-8
LO Frequency	869		960	MHz	VCOHL=0
	1805		1990	MHz	VCOHL=1
Output Level to Synth	-18.6	-17.4	-16.2	dBm	2k $\Omega$ /5pF load
Output Frequency to Synth	434.5		497.5	MHz	VCO_OUT=VCO/8
Tuning Voltage	0.5		2.0	V	
Tuning Line Input Impedance		12		M $\Omega$	DC measurement
$K_{VCO}$ *	-27		-107	MHz/V	
LO Phase Noise, Low Band					GSM850/EGSM
0.6MHz		-129.2	-127.2	dBc/Hz	
1.6MHz		-138.4	-136.4	dBc/Hz	
3.0MHz		-142.8	-140.8	dBc/Hz	
10.0MHz		-145.0	-143.0	dBc/Hz	
LO Phase Noise, High Band					DCS/PCS
0.6MHz		-123.0	-121.0	dBc/Hz	
1.6MHz		-133.1	-131.1	dBc/Hz	
3.0MHz		-137.9	-135.9	dBc/Hz	
10.0MHz		-140.0	-138.0	dBc/Hz	
* When used with an RF600X, the product of $K_{VCO}$ xCharge Pump Current is calibrated to be within 5% of nominal value.					

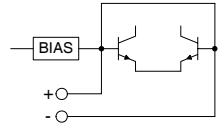
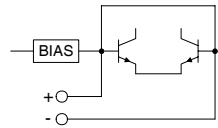
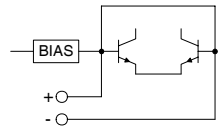
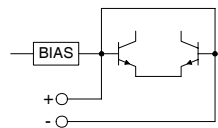
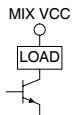
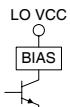
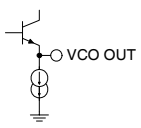
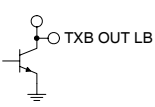
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Polyphase Filter (4th Order)</b>					
VLIF Mode					
Center Frequency	99.5	107.0	114.5	kHz	
Half-Bandwidth	180	200	220	kHz	
In-Band Ripple			0.35	dB	130 kHz Half-Bandwidth
Group Delay			1.3	us	130 kHz Half-Bandwidth
Integrated Attenuation					
200 kHz	5.0			dB	
400 kHz	23.0			dB	
600 kHz	38.0			dB	
>600 kHz	38.0			dB	
I/Q Phase Error		1.0	1.8	°	Entire RX chain
I/Q Amplitude Error		0.1	0.25	dB	Entire RX chain
Output Capacitive Load			20	pF	
Output Resistive Load		30		kΩ	30 kΩ RF6001/3 RX A/D input impedance.
Maximum Output Voltage Swing	1			V <sub>P,P</sub>	Differential
Output Common Mode Voltage	1.23	1.26	1.29	V	
Static DC Offset	-160		+160	mV	Uncorrected
Direct Conversion (DCR) Mode					
Center Frequency	-7.5	0	+7.5	kHz	
Half-Bandwidth	180	200	220	kHz	
In-Band Ripple			0.35	dB	130 kHz Half-Bandwidth
Group Delay			1.3	us	130 kHz Half-Bandwidth
Integrated Attenuation					
200 kHz	5.0			dB	
400 kHz	23.0			dB	
600 kHz	38.0			dB	
>600 kHz	38.0			dB	
I/Q Phase Error		1.0	1.8	°	Entire RX chain
I/Q Amplitude Error		0.1	0.25	dB	Entire RX chain
Output Capacitive Load			20	pF	
Output Resistive Load		30		kΩ	30 kΩ RF6001/3 RX A/D input impedance.
Maximum Output Voltage Swing	1			V <sub>P,P</sub>	Differential
Output Common Mode Voltage	1.20	1.23	1.26	V	
DC Offset (Uncorrected)	-160		+160	mV	Uncorrected

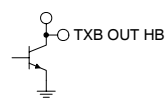
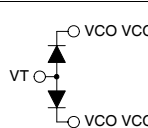
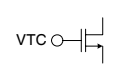
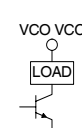
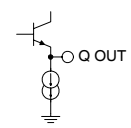
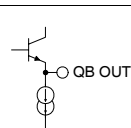
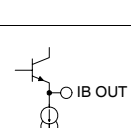
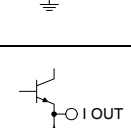
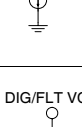
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Polyphase Filter (4th Order), cont'd</b>					
<b>Polyphase Input Attenuator (DCR) (Midband Gain)</b>					
Gain	-0.3	0	+0.3	dB	C_G1_1:0=11
	-6.1	-5.5	-4.9	dB	C_G1_1:0=10
	-14.0	-13.0	-12.0	dB	C_G1_1:0=00
<b>First Pole (DCR) (Midband Gain)</b>					
Gain	18.6	18.7	18.8	dB	F_G1_3:0=0111
	17.5	17.6	17.7	dB	F_G1_3:0=0110
	16.5	16.6	16.7	dB	F_G1_3:0=0101
	15.5	15.6	15.7	dB	F_G1_3:0=0100
	14.5	14.6	14.7	dB	F_G1_3:0=0011
	13.5	13.6	13.7	dB	F_G1_3:0=0010
	12.5	12.6	12.7	dB	F_G1_3:0=0001
	11.5	11.6	11.7	dB	F_G1_3:0=0000
	10.4	10.5	10.6	dB	F_G1_3:0=1111
	9.4	9.5	9.6	dB	F_G1_3:0=1110
	8.4	8.5	8.6	dB	F_G1_3:0=1101
	7.4	7.5	7.6	dB	F_G1_3:0=1100
	6.4	6.5	6.6	dB	F_G1_3:0=1011
	5.4	5.5	5.6	dB	F_G1_3:0=1010
	4.4	4.5	4.6	dB	F_G1_3:0=1001
	3.4	3.5	3.6	dB	F_G1_3:0=1000
<b>Second Pole (DCR) (Midband Gain)</b>					
Gain	7.3	7.4	7.6	dB	S_G2_0=1
	-0.9	-0.7	-0.5	dB	S_G2_0=0
<b>Third Pole (DCR) (Midband Gain)</b>					
Gain	0.9	1.0	1.1	dB	S_G2_1=1
	-6.9	-6.8	-6.7	dB	S_G2_1=0
<b>Fourth Pole (DCR) (Midband Gain)</b>					
Gain	13.9	14.3	14.7	dB	S_G3_1:0=11
	8.1	8.4	8.7	dB	S_G3_1:0=01
	2.2	2.5	2.8	dB	S_G3_1:0=00

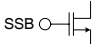
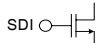
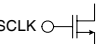
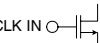
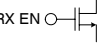
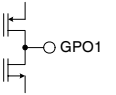

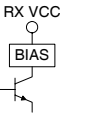


Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>DC Offset Correction</b>					
Residual DC Error	-20		+20	mV	Following DC offset correction. Differential measurement.
DC Correction Time			20	μs	
DC Offset Drift Referred to the LNA Input			-126	dBm	Max gain measured in a window 150μs to 730μs after RXEN is activated.
CLK IN Frequency		26		MHz	CLKF=0
<b>TX Buffer</b>					
Low Band					
Input Power	3		6	dBm	
Saturated Output Power	6.6	7.7	8.8	dBm	P <sub>IN</sub> = +4 dBm
Output Power Variation	-1.1		1.1	dB	
DC Current Drain	5.2	7.2	9.3	mA	DC with no RF input
RF Current Drain	14	19.5	25	mA	P <sub>IN</sub> = +4 dBm
Phase Noise	-167			dBc/Hz	20MHz offset
Input VSWR		3:1			P <sub>IN</sub> = +4 dBm
Output VSWR			2:1		P <sub>IN</sub> = +4 dBm
Load VSWR			3:1		P <sub>IN</sub> = +4 dBm
Reverse Isolation	20			dB	TXEN = H
Forward Isolation	20			dB	TXEN = L
High Band					
Input Power	3		6	dBm	
Saturated Output Power	4.9	6.5	8.1	dBm	P <sub>IN</sub> = +4 dBm
Output Power Variation	-1.6		1.6	dB	
DC Current Drain	8	11	13.8	mA	DC with no RF input
RF Current Drain	18	24.5	32	mA	P <sub>IN</sub> = +4 dBm
Phase Noise	-160			dBc/Hz	
Input VSWR		3:1			P <sub>IN</sub> = +4 dBm
Output VSWR			2:1		P <sub>IN</sub> = +4 dBm
Load VSWR			3:1		P <sub>IN</sub> = +4 dBm
Reverse Isolation	35			dB	TXEN = H
Forward Isolation	28			dB	TXEN = L

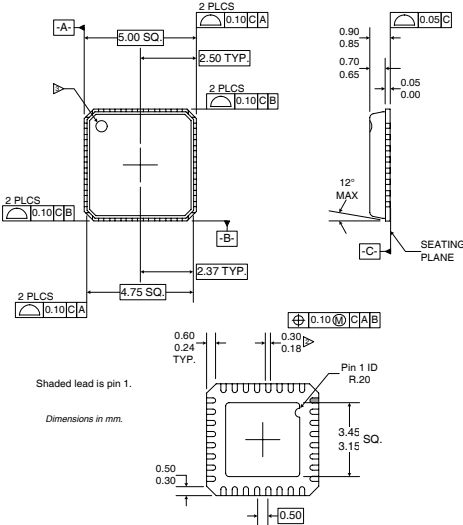
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Serial Interface</b>					Applies to pins SCLK, SDI and SSB.
Input High Voltage ( $V_{IH}$ )	$0.7 * V_{CC}$			V	
Input Low Voltage ( $V_{IL}$ )			$0.3 * V_{CC}$	V	
Input High Current ( $I_{IH}$ )			5	$\mu A$	
Input Low Current ( $I_{IL}$ )			5	$\mu A$	
Setup Time ( $T_{SU}$ )	25			ns	
Hold Time ( $T_H$ )	10			ns	
Rise/Fall Time ( $T_{RF}$ )			10	ns	
Clock to Select Time ( $T_{CS}$ )	10			ns	
Clock Pulse Width High ( $T_{CWH}$ )	50			ns	
Clock Pulse Width Low ( $T_{CWL}$ )	50			ns	
<b>Digital Output Drivers</b>					Apply to pins: GPO1, GPO2
Output High Voltage ( $V_{OH}$ )	$V_{CC}-0.05$			V	1 mA load
	$V_{CC}-0.50$			V	10 mA load
Output Low Voltage ( $V_{OL}$ )			0.05	V	1 mA load
			0.50	V	10 mA load
Output Rise/Fall Time ( $T_{RFO}$ )			5	ns	
<b>26MHz Reference Clock Input</b>					Applies to CLKIN.
Frequency Range ( $F_R$ )		26		MHz	
Input Level ( $V_{INR}$ )	600			mV <sub>P-P</sub>	AC-coupled mode
Input Impedance ( $Z_{INR}$ )		49k $\Omega$ // 480fF			
Interface Voltage		$V_{CC}/2$		V	Internal bias
Transient Startup Time		250		ns	
Input High Voltage ( $V_{IH}$ )	$0.7 V_{CC}$			V	DC-coupled mode
Input Low Voltage ( $V_{IL}$ )			$0.3 V_{CC}$	V	DC-coupled mode

Pin	Function	Description	Interface Schematic
1	LNA 1P	RF input to LNA 1. Internally matched for 800MHz to 1000MHz operation. This pin possesses a DC voltage with respect to ground, and a series blocking cap may be required in some applications.	
2	LNA 1N	Complementary input to pin 1. This pin possesses a DC voltage with respect to ground, and a series blocking cap may be required in some applications.	See Pin 1.
3	LNA 2P	RF input to LNA 2. Internally matched for 800MHz to 1000MHz operation. This pin possesses a DC voltage with respect to ground, and a series blocking cap may be required in some applications.	
4	LNA2N	Complementary input to pin 3. This pin possesses a DC voltage with respect to ground, and a series blocking cap may be required in some applications.	See Pin 3.
5	LNA 3P	RF input to LNA 3. Internally matched for 1800MHz to 2000MHz operation. This pin possesses a DC voltage with respect to ground, and a series blocking cap may be required in some applications.	
6	LNA 3N	Complementary input to pin 5. This pin possesses a DC voltage with respect to ground, and a series blocking cap may be required in some applications.	See Pin 5.
7	LNA 4P	RF input to LNA 4. Internally matched for 1800MHz to 2000MHz operation. This pin possesses a DC voltage with respect to ground, and a series blocking cap may be required in some applications.	
8	LNA 4N	Complementary input to pin 7. This pin possesses a DC voltage with respect to ground, and a series blocking cap may be required in some applications.	See Pin 7.
9	MIX VCC	Supply for the quadrature mixer.	
10	LO VCC	VCO divider supply.	
11	VCO OUT	Output from the VCO to drive the synthesizer input. This is the VCO divided by 8.	
12	TXB OUT LB	Low band TX buffer output.	

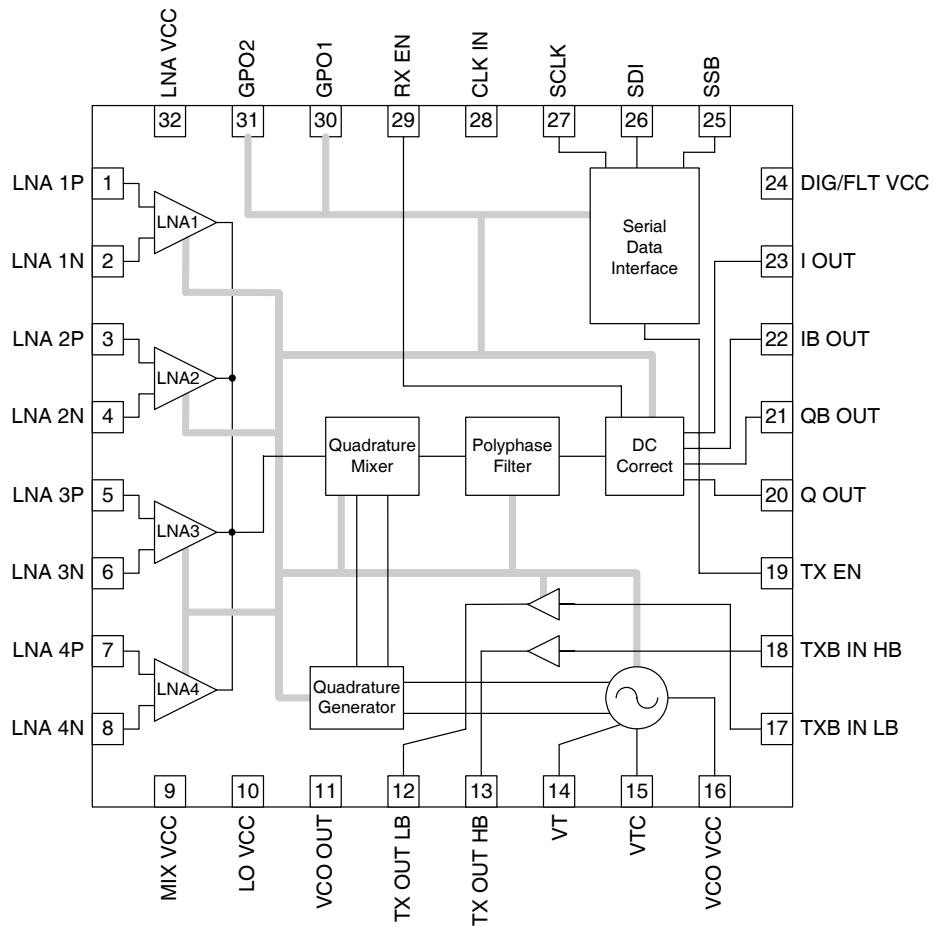
Pin	Function	Description	Interface Schematic
13	TXB OUT HB	High band TX buffer output.	
14	VT	Tuning control line for the VCO. Analog input.	
15	VTC	Coarse VCO tuning control driven by RF6001. Digital input.	
16	VCO VCC	Supply for the RF VCO.	
17	TXB IN LB	TX buffer low band input. This is a high impedance voltage-driven input designed to be driven by the RF6001/3 TXVCO output.	
18	TXB IN HB	TX buffer high band input. This is a high impedance voltage-driven input designed to be driven by the RF6001/3 TXVCO output.	
19	TX EN	TX buffer enable. If the TX SEL (CRX1[2]) bit is set high, the TX buffers are enabled by this pin. If the TX SEL bit is set low, this pin has no effect on the activation of the TX buffers. (See register map for more information.) The TX buffers are enabled by setting this pin high. The TX buffers are disabled by setting this pin low.	
20	Q OUT	Q-channel differential IF output.	
21	QB OUT	Complementary output to Q OUT.	
22	IB OUT	Complementary output to I OUT.	
23	I OUT	I-channel differential IF output.	
24	DIG/FLT VCC	Supply for all digital circuitry. Supply for the filter.	

Pin	Function	Description	Interface Schematic
25	<b>SSB</b>	SDI enable input (active low).	
26	<b>SDI</b>	SDI data input.	
27	<b>SCLK</b>	SDI clock input.	
28	<b>CLK IN</b>	Clock input for the DC offset correction system. A 26MHz clock must be applied to this pin for proper operation of the DC offset correction system.	
29	<b>RX EN</b>	Set to VCC to activate the IC. Set to GND to deactivate.	
30	<b>GPO1</b>	General purpose digital output 1. Controlled via SDI programming.	
31	<b>GPO2</b>	General purpose digital output 2. Controlled via SDI programming.	
32	<b>RX VCC</b>	Supply for the LNA's.	

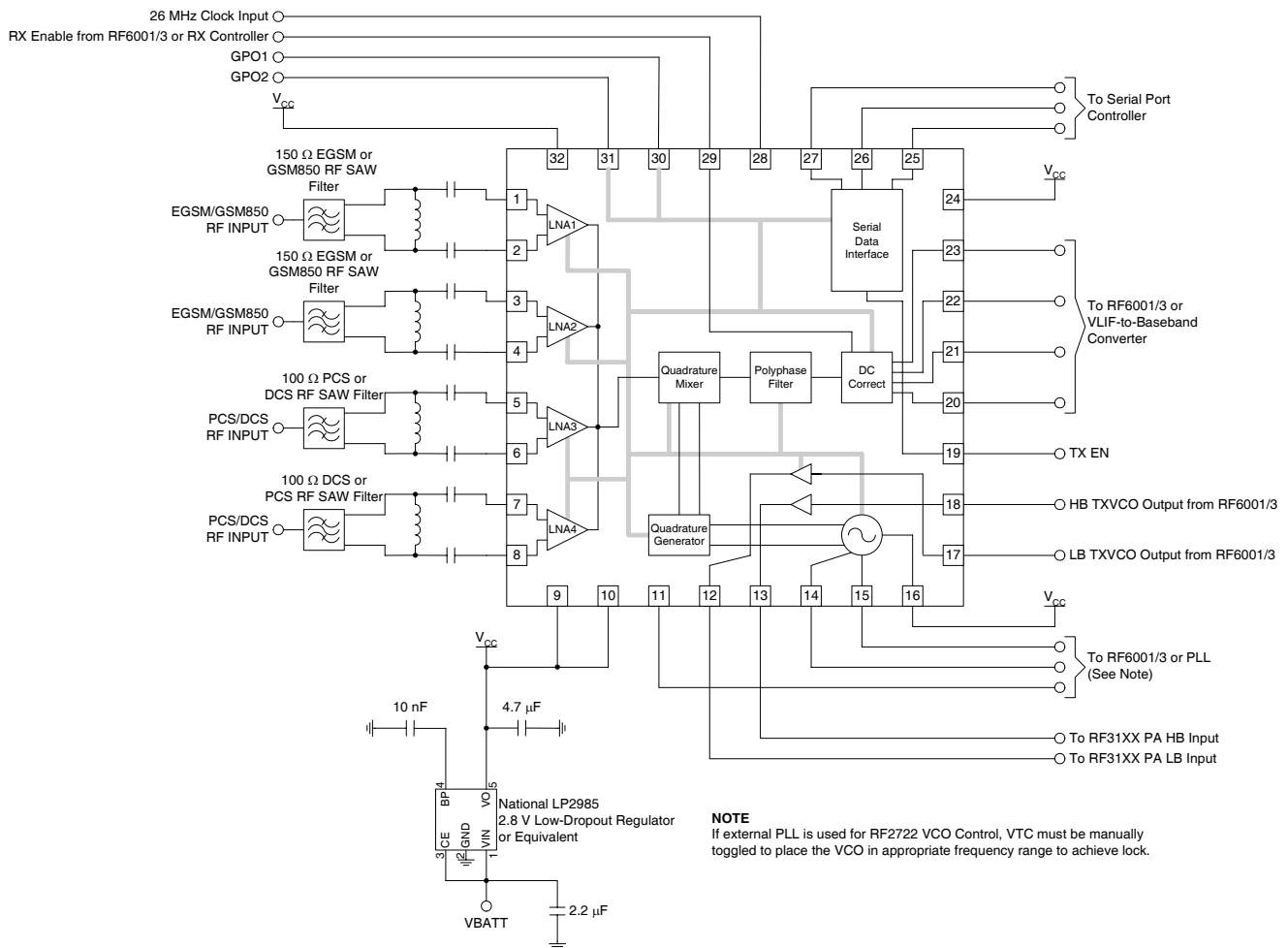
Package Drawing



**Detailed Functional Block Diagram**



## Application Schematic





## Application Information

### Functional Description

The RF2722 receiver IC will support GSM and EDGE cellular standards.

Four Low Noise Amplifiers (LNA's) are provided to accommodate various combinations of up to four bands. The four LNA's share a common quadrature mixer. The active LNA is selected and may be bypassed through the Serial Data Interface (SDI).

An RX Local Oscillator (VCO) is provided. The VCO is fully integrated including an internal resonator and is band-selectable to cover the GSM850, EGSM, DCS, and PCS bands.

The desired signal is converted to either a VLIF (100kHz/120kHz) or directly to DC, as determined by the setting of bit 1 in SDI register CF.

Once downconverted, the signal is filtered by an active RC Polyphase bandpass filter. The purpose of this filter is to provide some rejection to interfering signals such that the dynamic range of the A/D converters will not be compromised.

The RF2722 also includes two reverse isolation dual-band buffer amplifiers. These buffers are suitable for use in the transmit path between the VCO output and the PA input to improve transmit performance. The RF2722 accepts single-ended inputs from the RF6001/3 and provides single-ended outputs to the PA.

### DC Correction Operation

The Polaris RF2722 VLIF/DCR IC will reduce the residual DC error of the I and Q channels to less than 20mV within 20usec assuming that no input signal is present during the DC adapt time. The DC correction system will activate on the rising edge of RX\_EN if the SDI bit DC\_EN is programmed true. Programming the SDI bit DC\_ST true can also activate the DC correction system. In this case the SDI bit DC\_ST will automatically return to a false state once the DC correction system is activated.

The RF6001/3 also has an RX\_EN pin that normally is set high at the same time as the RX\_EN of the RF2722.

The DC correction system of the RF2722 will run for DC\_TIME1 cycles of the clock present on CLK\_IN divided by 16. This should be set for approximately 20usec. With a 26MHz clock on CLK\_IN the setting of DC\_TIME1 will be 20H. Given the low levels of LO leakage to the LNA inputs of the RF2722, the coarse DC adapt will be performed when RX\_EN rises with the LNAs disabled. The residual DC error due to LO leakage when the LNAs are enabled will be less than 5mV. Once completed the DC correction outputs of the RF2722 will be held until power is removed from the IC or until another DC correction command is issued.

During operation of the DC correction system the input signal should be muted so that the coarse DC correction system does not attempt to lock to the instantaneous signal level. This can be accomplished by disabling all LNAs. This mode is selected if the LND SDI bit is programmed true. This is performed for DC\_TIME2 clock cycles of CLK\_IN divided by 16 beginning at the DC correction command time so that the RF2722 will have sufficient time to complete DC correction.

If the radio employs a T/R switch then the T/R switch can also be used to disable the signal instead of or in addition to disabling the LNAs. The RF2722 can be used to automatically disable the T/R switch if the SDI bit TRD is programmed true. In this case it is assumed that GPO1 and GPO2 provide on/off control for each of the possible bands of the receive side of the T/R switch. During the DC control time interval set by DC\_TIME2 the outputs of GPO1 and GPO2 will be overridden by the SDI register TRDC. The bits of this register can be set to 0 or 1 as needed by the particular T/R switch implementation to deactivate the receiver inputs. After DC\_TIME2 has expired the normally programmed GPO states will return.

After the coarse DC adapt time has elapsed then the RF6001/3 will require an additional time of approximately 50usec to complete the fine digital DC correction.

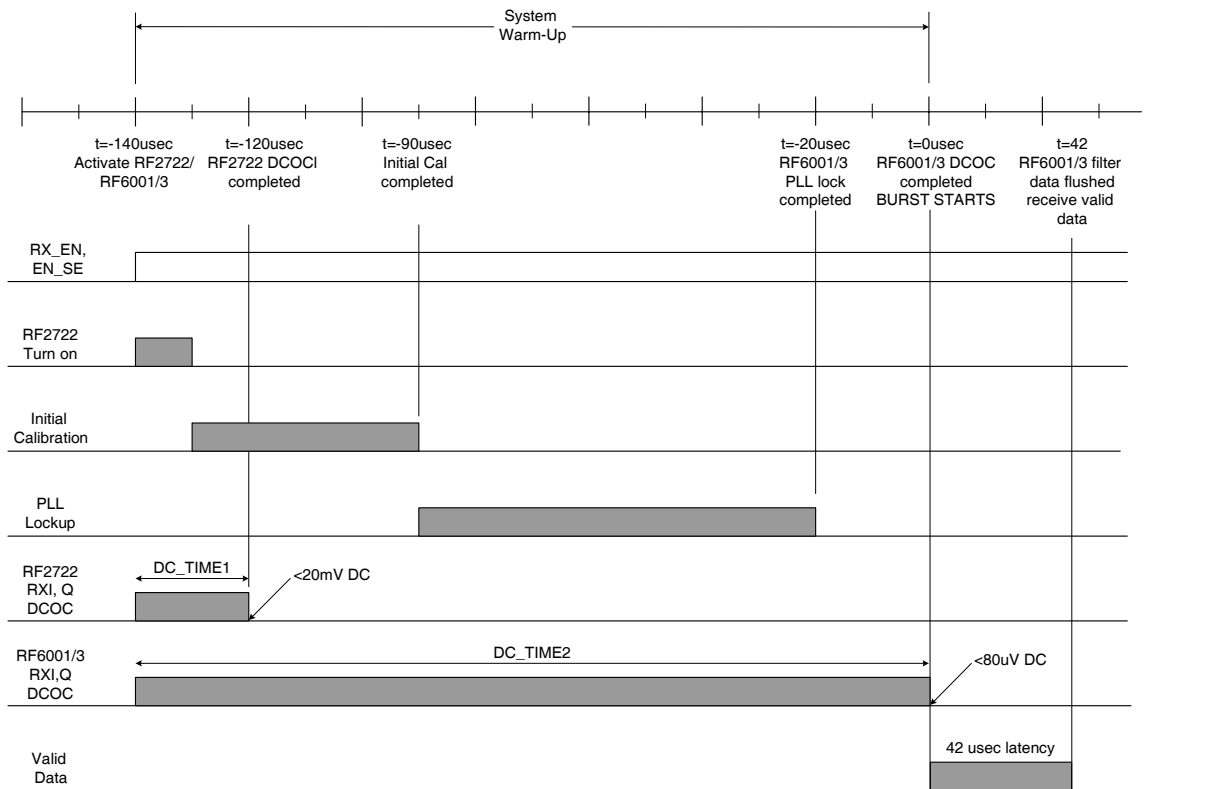
Note that the input signal may be present during the final DC correction time of the RF6001/3. For VLIF modes this will not cause a DC problem since the RF6001/3 does an averaging of the DC error and there will be few components of the signal

near DC. In addition, the RF6001/3 will notch out 100kHz converted DC components for channel bandwidths less than or equal to 85kHz. The RF6003 will also notch out 120kHz converted DC components for channel bandwidth of 90kHz. This is only useful in VLIF mode.

In DCR mode there may be significant spectral content near DC during the final adapt of the RF6001/3. This may result in a significant DC component that will track the input desired signal level. It is assumed that the baseband DSP will be able to remove any such static DC error. In addition, if the DC adapt of the RF6001/3 is performed during the guard times then the spectral content of the input signal should be a tone in the region of 50kHz to 70kHz and should not interfere with the DC adapt process.

If DC\_TIME2 is extended to encompass the fine DC adapt time of the RF6001/3 then the input signal will not interfere with the adapt process as the LNAs will be muted. However, if there is any residual LO leakage into the LNA input then this error will remain after the DC correction process. This may be a smaller residual error than that due to the input signals.

A diagram depicting the composite DC correction and RX startup of the RF2722 and RF6001/3 is presented below.



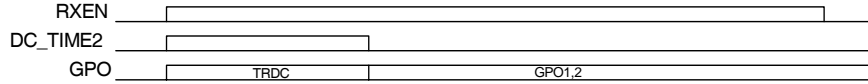
### GPO Control

The RF2722 allows the GPOs to switch to an alternate setting defined by TRDC during RX DC offset correction when TRD is programmed high. This is triggered by the rising edge of RX\_EN pin and terminated by the expiration of DC\_TIME2 in the RF2722. This mode of operation is used to turn off the LNAs or redirect the T/R switch to TX mode during the DCOC time interval so that the signal present from the previous time slot or LO leakage will not cause an error in the DCOC.

In TX mode the RF2722 can also switch to an alternate set of GPO settings defined by TRTXA at the rising edge of TX\_EN pin when TRTX\_EN is programmed high. This functionality is used to redirect the T/R switch to RX mode during the synthesizer lock time so that the PA output due to feed-through from the VCO will not violate the ETSI time-mask specification.

RX Mode

When RXEN rises, DC\_TIME2 starts in the RF2722 and the part switches to the alternate GPO settings defined in TRDC. Once the timer expires then the settings of the GPO's revert back to the originally programmed GPO SDI fields.



TX Mode

When TXEN rises, the RF2722 GPOs switch to the alternate GPO settings defined in TRTXA. When TXEN falls, the RF2722 GPO settings revert back to the originally programmed GPO SDI fields.



**Device Control and Programming**

The Polaris RF2722 VLIF/DCR IC provides a serial interface for programming the control settings. The interface consists of eight registers that are accessed individually via a six-bit address word. (Two registers are unused at this time and are included for future expansion.) The register map is shown below. Each register plus the six address bits requires an 18-bit transfer (except register CF, which has 18 bits and so requires a 24-bit transfer). Additional 'padding' bits can be added between the address bits and the data bits, if longer transfer lengths are needed. Since the RF2722 will be most likely used with the RF6001/3 then it is expected that six such padding bits will be used in each transfer to bring the total number of bits up to 24. This will then match the programming width of the RF6001/3.

Address	Register	Description
100000	CRX1	AGC, standby modes, LO phase cal
100001	CRX2	DCOC and GPO
100010	CRX3	DCOC
100011	CRX4	DCOC
100100	CRX5	LNA, VCO, mixer current settings, Gain cal
100101	CF	Gain settings for the polyphase filters and LNA's.
100110	Reserved	Reserved for future use.
100111	Reserved	Reserved for future use.
011111	Reset	Writing this address resets all SDI bits to their default states.



**Receiver Configuration Register 1 (CRX1) - Address 100000**

Location	Bit Name	Default	Description
CRX1(11)	reserved	0	Reserved
CRX1(10:7)	LO_PH_CAL	0000	I/Q Phase Calibration
CRX1(6)	CLK BYP	1	If set to zero, then the CLK_IN pin is AC-coupled. If set to one, then the CLK_IN pin is DC-coupled.
CRX1(5)	CLKF	0	Input clock frequency select. (Must be set to 26MHz for normal operation.) Programming this bit high activates a divide-by-two function on the CLK_IN pin. Programming this bit low deactivates the divide-by-two function. The DC offset correction circuitry requires a 26MHz clock for proper operation. Therefore, CLKF should be programmed low if a 26MHz clock is provided to the CLK_IN pin. 0=CLK_IN frequency is 26MHz 1=CLK_IN frequency is 52MHz
CRX1(4)	VCOSEL	0	When set to zero, the VCO is turned on and off by RX_EN. When programmed high, the VCO is controlled by the VCOEN bit instead of RX_EN.
CRX1(3)	VCOEN	0	When VCOSEL is set to one, then VCOEN turns on and off the VCO. When VCOEN is set to zero, the VCO is off. When VCOEN is set to one, the VCO is turned on.
CRX1(2)	TXSEL	1	If programmed high, the TX buffers are enabled by the TX_EN pin. If programmed low, the TX buffers are enabled by CF[16].
CRX1(1:0)	TEST	00	Test Output Selection Bits: The GPO1 pin provides test signal outputs as well as the activation signal for the RF6001 RX system. The available signals are shown below. 00 Normal output of GPO1 pin 01 Serial data shifting through Configuration Registers 10 MSB bit of the VCO calibration counter 11 dcadapt counter 2 output

**Receiver Configuration Register 2 (CRX2) - Address 100001**

Programming Bits	# of Bits	Default	Description
CRX2(11)	DC_ST	0	If programmed high, the DC correction system is activated when the SDI word is loaded. DC_ST will revert low once the DC correction system is activated. RX EN needs to be high for DC_ST to operate correctly.
CRX2(10)	DC_EN	1	If programmed high, the DC correction system is activated on the rising edge of RX_EN (default=1).
CRX2(9)	LND	0	If programmed high, the LNA's are disabled during the time interval of the DC correction system.
CRX2(8)	TRD	0	If programmed high, GPO1 and GPO2 follow TRDC instead of the normal GPO programming during the time interval defined by DC_TIME2.
CRX2(7)	TRTX_EN	0	If programmed high, the functionality defined by TRTXA is active.
CRX2(6)	reserved	0	Reserved
CRX2(5:4)	TRDC	00	If TRD is set true, then during the time interval defined by DC_TIME2, GPO1 and GPO2 are reassigned as follows. GPO1=TRDC[0] GPO2=TRDC[1]
CRX2(3:2)	TRTXA	00	If TRTX_EN is programmed high, while TXEN pin is high the GPO outputs are reassigned as follows: GPO1=TRTXA[0] GPO2=TRTXA[1]
CRX2(1:0)	GPO	00	The states of each bit within this word are transferred to the corresponding GPO pin as follows. GPO1=GPO[0] GPO2=GPO[1]

### Receiver Configuration Register 3 (CRX3) - Address 100010

Programming Bits	# of Bits	Defaults	Description
CRX3(11:10)	reserved	00	Reserved
CRX3(9:2)	DC_TIME1	20H	Sets the number of 26MHz/16 clock cycles from activation until the RF2722 DCOC system is frozen.
CRX3(1:0)	reserved	00	Reserved

### Receiver Configuration Register 4 (CRX4) - Address 100011

Programming Bits	# of Bits	Defaults	Description
CRX4(11:10)	reserved	00	Reserved
CRX4(9:0)	DC_TIME2	124H	Sets the number of 26MHz/16 clock cycles from activation until the LNA's and/or the RX T/R switch are reactivated.

### Receiver Configuration Register 5 (CRX5) - Address 100100

Programming Bits	# of Bits	Defaults	Description															
CRX5(11:9)	Gain_Cal	011	I/Q Gain Calibration															
CRX5(8:6)	Reserved	000	Reserved															
CRX5(5:4)	Reserved	00	Reserved															
CRX5(3:2)	LNA_CURR	10	These bits control the LNA current as shown below. <table style="margin-left: 20px;"> <tr> <td></td> <td>Low Band</td> <td>High Band</td> </tr> <tr> <td>00</td> <td>11mA</td> <td>13.2mA</td> </tr> <tr> <td>01</td> <td>12.8mA</td> <td>15mA</td> </tr> <tr> <td>10</td> <td>14.6mA</td> <td>16.9mA</td> </tr> <tr> <td>11</td> <td>16.4mA</td> <td>18.7mA</td> </tr> </table>		Low Band	High Band	00	11mA	13.2mA	01	12.8mA	15mA	10	14.6mA	16.9mA	11	16.4mA	18.7mA
	Low Band	High Band																
00	11mA	13.2mA																
01	12.8mA	15mA																
10	14.6mA	16.9mA																
11	16.4mA	18.7mA																
CRX5(1:0)	MIX_CURR	10	These bits control the Mixer current as shown below. <table style="margin-left: 20px;"> <tr> <td>00</td> <td>12.5mA</td> </tr> <tr> <td>01</td> <td>13.5mA</td> </tr> <tr> <td>10</td> <td>14.4mA</td> </tr> <tr> <td>11</td> <td>15.6mA</td> </tr> </table>	00	12.5mA	01	13.5mA	10	14.4mA	11	15.6mA							
00	12.5mA																	
01	13.5mA																	
10	14.4mA																	
11	15.6mA																	

### Polyphase Filter Gain Register (CF) - Address 100101

Programming Bits	# of Bits	Defaults	Description																																
CF(17)	TX_HL	0	If programmed low, enables Cellular/GSM TX buffer. If programmed high, enables PCS/DCS TX buffer.																																
CF(16)	TX_EN	0	If TX_SEL is set false, TX buffers are controlled by this bit.																																
CF(15:13)	LNA_SEL	101	Selects the active LNA. <table style="margin-left: 20px;"> <tr> <td>000</td> <td>LNA1 (US/GSM)</td> </tr> <tr> <td>001</td> <td>LNA2 (US/GSM)</td> </tr> <tr> <td>010</td> <td>LNA3 (DCS/PCS)</td> </tr> <tr> <td>011</td> <td>LNA4 (DCS/PCS)</td> </tr> <tr> <td>100</td> <td>All LNA's off</td> </tr> <tr> <td>101</td> <td>All LNA's off</td> </tr> </table>	000	LNA1 (US/GSM)	001	LNA2 (US/GSM)	010	LNA3 (DCS/PCS)	011	LNA4 (DCS/PCS)	100	All LNA's off	101	All LNA's off																				
000	LNA1 (US/GSM)																																		
001	LNA2 (US/GSM)																																		
010	LNA3 (DCS/PCS)																																		
011	LNA4 (DCS/PCS)																																		
100	All LNA's off																																		
101	All LNA's off																																		
CF(12)	VCOHL	0	If programmed low, divides the VCO by 2 and routes signal through US Cellular/GSM filter path. If programmed high, the VCO signal is routed through PCS/DCS filter path.																																
CF(11:8)	F_G1	0000	Selects the fine gain setting of the first pole of the filter. The gain in dB at the mid-band (0Hz for DCR) is as shown below. <table style="margin-left: 20px;"> <tr> <td>0000</td> <td>= 11.6dB</td> <td>0001</td> <td>= 12.6dB</td> <td>0010</td> <td>= 13.6dB</td> <td>0011</td> <td>= 14.6dB</td> </tr> <tr> <td>0100</td> <td>= 15.6dB</td> <td>0101</td> <td>= 16.6dB</td> <td>0110</td> <td>= 17.6dB</td> <td>0111</td> <td>= 18.7dB</td> </tr> <tr> <td>1000</td> <td>= 3.5dB</td> <td>1001</td> <td>= 4.5dB</td> <td>1010</td> <td>= 5.5dB</td> <td>1011</td> <td>= 6.5dB</td> </tr> <tr> <td>1100</td> <td>= 7.5dB</td> <td>1101</td> <td>= 8.5dB</td> <td>1110</td> <td>= 9.5dB</td> <td>1111</td> <td>= 10.5dB</td> </tr> </table>	0000	= 11.6dB	0001	= 12.6dB	0010	= 13.6dB	0011	= 14.6dB	0100	= 15.6dB	0101	= 16.6dB	0110	= 17.6dB	0111	= 18.7dB	1000	= 3.5dB	1001	= 4.5dB	1010	= 5.5dB	1011	= 6.5dB	1100	= 7.5dB	1101	= 8.5dB	1110	= 9.5dB	1111	= 10.5dB
0000	= 11.6dB	0001	= 12.6dB	0010	= 13.6dB	0011	= 14.6dB																												
0100	= 15.6dB	0101	= 16.6dB	0110	= 17.6dB	0111	= 18.7dB																												
1000	= 3.5dB	1001	= 4.5dB	1010	= 5.5dB	1011	= 6.5dB																												
1100	= 7.5dB	1101	= 8.5dB	1110	= 9.5dB	1111	= 10.5dB																												
CF(7:6)	C_G1	11	Selects the coarse input attenuation setting of the first pole of the filter. <table style="margin-left: 20px;"> <tr> <td>00</td> <td>= -13dB</td> <td>01</td> <td>= N/A</td> <td>10</td> <td>= -5.5dB</td> <td>11</td> <td>= 0dB</td> </tr> </table>	00	= -13dB	01	= N/A	10	= -5.5dB	11	= 0dB																								
00	= -13dB	01	= N/A	10	= -5.5dB	11	= 0dB																												

CF(5)	S_G2_0	1	Selects the gain setting at midband of the second filter stage. 0=-0.7 dB1=+7.4 dB
CF(4)	S_G2_1	1	Selects the gain setting at midband of the third filter stage. 0=-6.8 dB1=+1 dB
CF(3:2)	S_G3	00	Selects the gain setting at midband of the output buffer. 00=2.5 dB01=8.4 dB10=N/A11=14.3 dB
CF(1)	VDS	0	Selects VLIF mode if programmed low. Selects DCR mode if programmed high.
CF(0)	LNA_BYP	0	If set to zero, the LNA is active. If set to one, the LNA is bypassed with a front end gain reduction of: 11.9 dB in low band; 10.4 dB in high band.

## PCB Design Requirements

### PCB Surface Finish

The PCB surface finish used for RFMD's qualification process is electroless nickel, immersion gold. Typical thickness is 3µinch to 8µinch gold over 180µinch nickel.

### PCB Land Pattern Recommendation

PCB land patterns are based on IPC-SM-782 standards when possible. The pad pattern shown has been developed and tested for optimized assembly at RFMD; however, it may require some modifications to address company specific assembly processes. The PCB land pattern has been developed to accommodate lead and package tolerances.

### PCB Metal Land Pattern

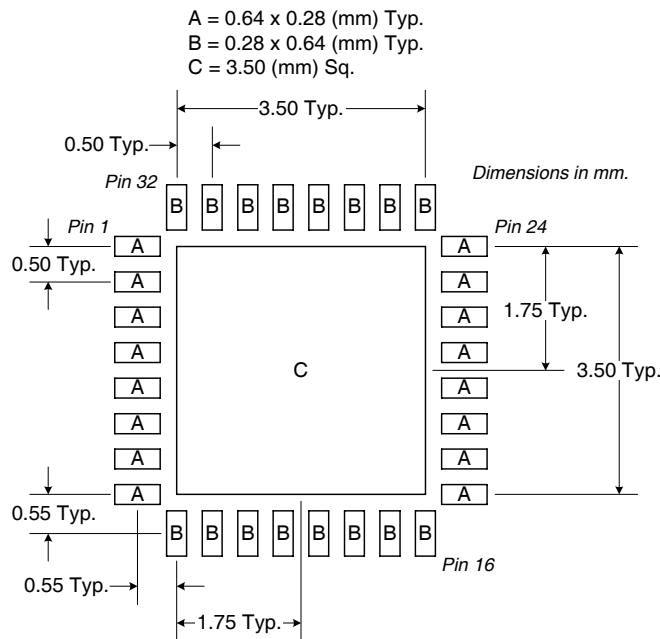


Figure 1. PCB Metal Land Pattern (Top View)



**PCB Solder Mask Pattern**

Liquid Photo-Imageable (LPI) solder mask is recommended. The solder mask footprint will match what is shown for the PCB metal land pattern with a 2mil to 3mil expansion to accommodate solder mask registration clearance around all pads. The center-grounding pad shall also have a solder mask clearance. Expansion of the pads to create solder mask clearance can be provided in the master data or requested from the PCB fabrication supplier.

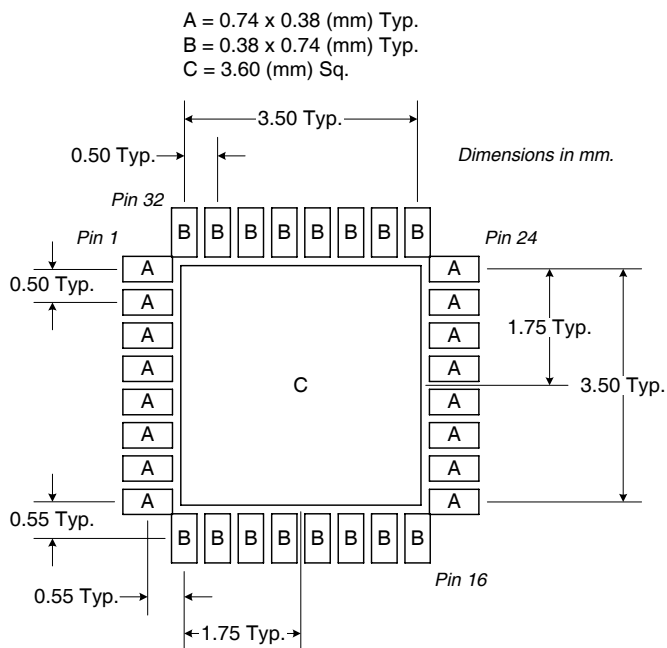


Figure 2. PCB Solder Mask (Top View)

**Thermal Pad and Via Design**

The PCB land pattern has been designed with a thermal pad that matches the exposed die paddle size on the bottom of the device.

Thermal vias are required in the PCB layout to effectively conduct heat away from the package. The via pattern shown has been designed to address thermal, power dissipation and electrical requirements of the device as well as accommodating routing strategies.

The via pattern used for the RFMD qualification is based on thru-hole vias with 0.203mm to 0.330mm finished hole size on a 0.5mm to 1.2mm grid pattern with 0.025mm plating on via walls. If micro vias are used in a design, it is suggested that the quantity of vias be increased by a 4:1 ratio to achieve similar results.

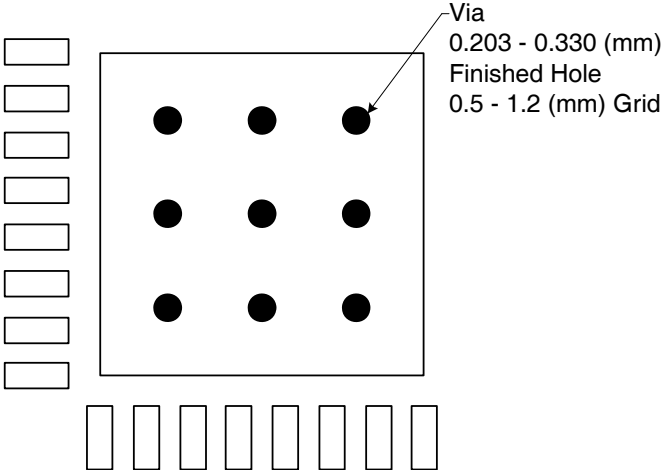


Figure 3. Thermal Pad and Via Design (RFMD Qualification)